EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	136384	(mocvd migration trench mask (grow growing grown)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 12:59
L2	0	(mocvd migration trench mask (grow growing grown)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/07/20 12:59
L3	1	(mocvd migration trench mask (grow or growing or grown)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/07/20 12:59
S1	2	("20050103259").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/09 17:48
S2	16754	MOCVD (Metal adj Organic adj Chemical adj Vapor adj Deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 17:49
S3	134	"100" near2 crystalline adj plane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 17:53
S4	7	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 17:50
S5	9377	"100" near2 (crystalline adj plane orientation lattice)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 17:53

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S6	4542	"100" near2 (crystalline adj plane orientation lattice crystal adj structure) and parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 17:54
S7	339	S2 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 17:55
S8	50113	selective adj area adj (growing growth) or SAG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:31
S9	9	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:23
S10	624	AlGaInAs	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:30
S11	1	S9 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:23
S12	257	S2 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:30
S13	245	AlGaInAs same laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:30

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S14	110	S12 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:43
S15	3	S14 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:31
S16	19	trench and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 19:43
S17	8	("4632723" | "5436192" | "5452383" | "5561079").PN. OR ("5728215"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/09 19:48
S18	121276	semiconductor near2 laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:30
S19	1194	S18 same MOCVD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:31
S20	897	trench same (second adj (mask window))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:31
S21	1	S19 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:32
S22	375	(selective controled) near2 growth with MOCVD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:51

EAST Search History

S23	153	S22 and (trench or etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:33
S24	7	("5872022").URPN.	USPAT	OR	ON	2006/04/09 20:47
S25	0	(selective controled) near2 growth with MOCVD same (trench and depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:52
S26	0	(selective controled) near2 growth same MOCVD same (trench and depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:52
S27	81	(selective controled) near2 growth same (trench and depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:06
S28	0	S27 and mocvd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/09 20:52
S29	338	438/481.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:14
S30	196	438/75.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:14
S31	60	438/189.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:14

EAST Search History

S32	889	438/200.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:14
S33	1141	S30 S31 S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:14
S34	916	S33 and (trench groove etch etching depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:21
S35	2	("5516283").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/10 09:21
S36	0	257/e21.566.ccls	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:42
S37	71	257/e21.566.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 09:43